



SDB3101F

Schottky Barrier Diode

Features

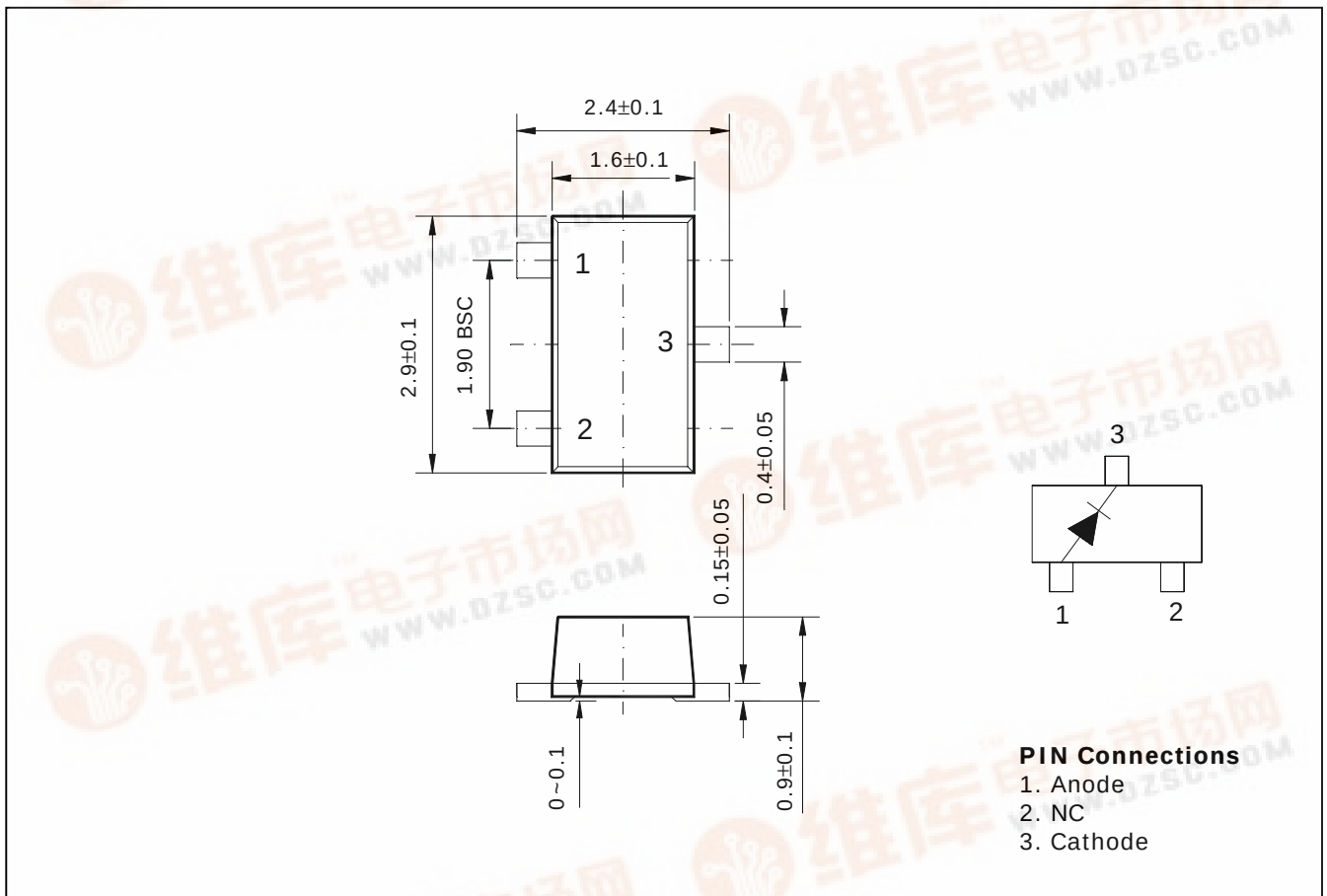
- Low power rectified
- Silicon epitaxial type
- High reliability

Ordering Information

Type No.	Marking	Package Code
SDB3101F	DB1	SOT-23F

Outline Dimensions

unit : mm



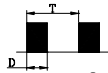
SDB3101F

Absolute maximum ratings

Ta=25°C

Characteristic	Symbol	Ratings	Unit
Reverse voltage	V_R	30	V
Repetitive peak forward current	I_{FRM}^*	0.5	A
Forward current	I_F	0.2	A
Non-repetitive peak forward current(10ms)	I_{FSM}	2	A
Power dissipation	P_D	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ 150	°C

* : $\delta = D/T = 0.33$
(T<1S)



Electrical Characteristics

Ta=25°C

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward voltage 1	$V_{F(1)}$	$I_F = 10\text{mA}$	-	-	0.4	V
Forward voltage 2	$V_{F(2)}$	$I_F = 30\text{mA}$	-	-	0.5	V
Reverse current	I_R	$V_R = 30\text{V}$	-	-	1	μA
Total capacitance	C_T	$V_R = 1\text{V}$, $f = 1\text{MHz}$	-	-	10	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10\text{mA}$, $I_{RR} = 1\text{mA}$, $R_L = 100\Omega$	-	-	5	ns

Electrical Characteristic Curves

Fig. 1 I_F - V_F

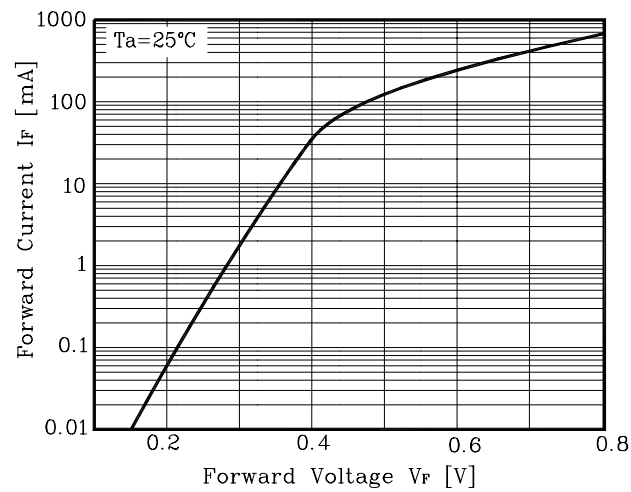


Fig. 2 I_R - V_R

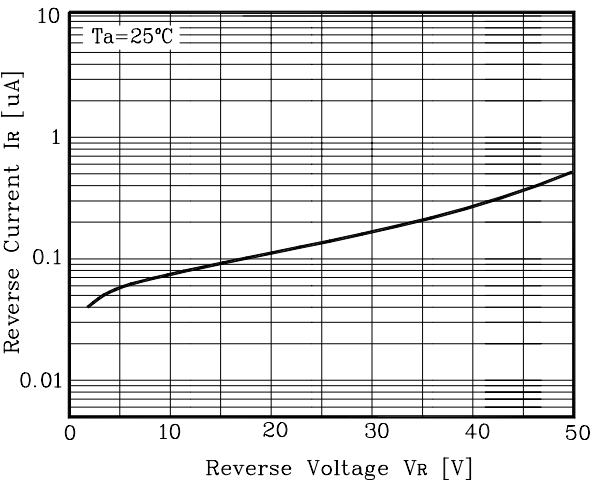


Fig. 3 C_T - V_R

